Persistence of Fourier Transform limited lines from a solid state quantum emitter in hexagonal Boron Nitride

A. Dietrich¹, M.W.Doherty², I. Aharonovich³, A. Kubanek∗,¹,⁴

¹ Institute for Quantum Optics, Ulm University, D-89081 Ulm, Germany
² Laser Physics Centre, Research School of Physics and Engineering Australian National University, Australian Capital Territory 2601, Australia
³ Institute of Biomedical Materials and Devices, Faculty of Science, University of Technology Sydney, Ultimo, New South Wales 2007, Australia
⁴ Center for Integrated Quantum Science and Technology (IQst), Ulm University, D-89081 Ulm, Germany

∗To whom correspondence should be addressed; E-mail: alexander.kubanek@uni-ulm.de

Solid state single photon sources with Fourier Transform (FT) limited lines are among the most crucial constituents of quantum photonic circuits, and have been subject of intensive research over the last decades. However, so far, all solid state systems only exhibit FT limited spectral lines at cryogenic temperatures due to strong interaction with the surrounding lattice via phonons. In this work, we demonstrate a solid state source of single photons that exhibit FT limited lines that persist all the way to room temperature. Our system is based on color center in atomically thin material, namely hexagonal boron nitride. Upon resonant excitation, we observe sub 100 MHz lines that persist across a temperature range of ≈ 300 K. Our results offer a significant development and new opportunities towards room temperature quantum circuitry, realization
of quantum repeaters and quantum information protocols.

Future applications of quantum technology rely on compact and scaleable quantum platforms. An essential building block for quantum information processing, e.g. quantum repeater, as well as quantum sensing or distributed quantum computing are single photon emitters (SPE) (1–4). Ideal quantum emitters stand out by on demand emission of exactly one photon per excitation pulse into a well-defined spatiotemporal mode where all photons are indistinguishable. Coherent photon absorption and emission is a fundamental prerequisite to ensure, for example, coherent read and write of quantum information in various proposed quantum protocols. Perfect coherence is achieved when all incoherent processes, such as electron-phonon interaction or dephasing via interaction with the environment, are suppressed. As a result the linewidth of the optical transition is fundamentally bound to the Fourier transform of the excited-state lifetime. This so-called Fourier transform (FT) limit can be achieved with cold atoms enabling single photon generation with high efficiency and indistinguishability but with limited rates (5). However, these systems require complex setup for atom trapping and cooling and ultra-high vacuum conditions.

To achieve progress with integrated solid state quantum systems, various quantum emitters have been heavily investigated. The interaction with the solid-state environment, in particular lattice vibrations or the nuclear bath, hinder to unfold their full potential and require cryogenic conditions to suppress the phononic vibration. Even at very low temperatures only a few systems including arsenic-based quantum dots (QDs) (6), color centers in solids (8,9), as well as single molecules (9) have shown FT limited spectral lines.

Here we show that a solid-state SPE exhibits FT limited lines at room temperature under resonant excitation. This observation demonstrates that nanoscale solid state systems can behave similarly to trapped atom/ions and at least for a fraction of time avoid interaction with the sur-
rounding phonons. Our results pave the way for scalable quantum applications under ambient conditions such as boson sampling (10), quantum communication (11), quantum simulation (12), linear quantum computing (13) and constitute the need to accelerate the studies into electron phonon processes of individual solid state systems.

The studied platform is a multilayer hexagonal boron nitride (hBN) flake that hosts optically active defects that can be harnessed as SPEs (14,15,16,17). Schematic illustration of the hBN lattice with the quantum emitter is show in figure 1A. hBN has recently shown impressive results as two-dimensional host for SPEs with many benefits arising from the two-dimensional nature. hBN has demonstrated the ability to host ultra bright, polarized quantum light sources with extremely high Debye-Waller factors. Moreover, the layered nature of the material has been carefully used to realize spectral tuning of the ZPL, using mechanical induced strain (18) or Stark tuning (19), to an extend of over 1.4 THz. These initial studies constitute a great promise for this platform to be extensively investigated as a promising building block for quantum photonic networks.

In the following we present two types of measurements, namely resonant photoluminescence excitation (PLE) spectroscopy and far off-resonant photoluminescence (PL) spectroscopy. These two measurements provide key elements to decouple the effects of phonon vibrations from the electronic transitions of the ZPL. On the one hand, under non-resonant excitation and at cryogenic temperatures, the PL spectrum shows spectral lines broadened due to electron-phonon interactions and spectral diffusion (20). Figure 1B shows an example of such a single emitter with FWHM of $\approx 177$ GHz and a Debye Waller factor of $\approx 0.8$.

On the other hand, probing the electronic transition via resonant, coherent excitation shows a PLE spectrum of the same emitter with an observed linewidth of $\approx 65$ MHz (figure 1C) corresponding to the FT limited linewidth of $(60.1 \pm 3.4)$ MHz (as extracted from the excited state lifetime of 2.65 ns (see (7)). The FT limited linewidth indicates the absence of dephasing or
Figure 1: Atomic defect in hexagonal boron nitride that acts as a single photon emitter. A: The electronic wavefunction of the defect center embedded in the hexagonal structure of Boron Nitride is illustrated as a ball-and-stick model. B: PL spectroscopy under far off-resonance excitation. The PL spectrum is dominated by a zero phonon line at 635.5 nm. The coupling of the electronic states to the phonon bath (the shaded area) and spectral diffusion broadens the line to a linewidth of 177 GHz. C: PLE spectroscopy under resonant excitation. Resonant excitation results in a homogeneous linewidth of $64.7 \pm 11.0$ MHz at 3 K within to the FT limit of $60.1 \pm 3.4$ MHz (7) (for details on FT limit see SI section 7).
Figure 2: Temperature-dependence in far off-resonant photoluminescence spectroscopy. A: Temperature-dependence of the PL ZPL energy. The significant shift in the ZPL energy by \( \approx 0.02 \) nm over a temperature range of 200 K indicates significant coupling to thermal expansion and electron-phonon interaction. B: Temperature-dependence of the PL ZPL linewidth. The PL ZPL linewidth shows a temperature-dependent broadening of \( \approx 4 \) THz over a temperature range of 300 K and is consistent with electron-phonon coupling (15).
other interaction with the solid state environment such as phonons on the timescale of \( \approx 0.04 \) s. We utilize the temperature dependent ZPL energy shift (figure 2A) and ZPL broadening (figure 2B) in PL to investigate the electron-phonon interaction of the defect center and the hBN host under off-resonant excitation. The ZPL broadening from 177 GHz at 3 K up to \( \approx 4 \) THz at 300 K shows phonon-mediated relaxation leading to incoherent photon emission \((21,15)\). The ZPL transition frequency similarly shows a significant shift from 471.65 THz at 3 K to 471.83 THz at 200 K. Such a behaviour is very common to solid state systems such as quantum dots and color centers in wide band gap materials. We describe the electron-phonon interaction by the deformation potential at the defect. A hBN monolayer (2D) is expected to be piezoelectric, whilst a bulk crystal (3D) is not due to inversion symmetry. For our intermediate situation of a multilayer flake there will be some degree of piezoelectricity, but we assume its contribution to be small. For a thin layer material there are three possible acoustic mode polarizations: flexural, shear and longitudinal. For the shift of the line position we include the effect of thermal expansion (see SI, section 2 for details on the model and the assumptions). The shift of the ZPL energy with temperature is related to the mean difference in thermal phonon energy between the ground and excited electronic states as well as the change in the electronic energies due to thermal expansion \((22)\) which leads to the odd powered polynomial

\[
E_{ZPL} \approx (e_{ZPL,1} + p_a a_1 + p_c c_1)T + (p_a a_2 + p_c c_2)T^2 + (e_{ZPL,3} + p_a a_3 + p_c c_3)T^3 \tag{1}
\]

The thermal expansion coefficients \( a_n \) and \( c_n \) are taken from X-Ray measurements \((23)\). \( p_a \) and \( p_c \) are the fitting parameters for the response of the defect to thermal expansion in the \( a \) and \( c \) directions. \( e_{ZPL,1} \) and \( e_{ZPL,3} \) are the electron-phonon fitting parameters corresponding to flexural (linear term) and shear/longitudinal modes (cubic term). We experimentally extract the coefficients to \( p_a \approx 0 \), \( p_c \approx 0 \), \( e_{ZPL,1} \approx 0 \) nm/K and \( e_{ZPL,3} = -3.2 \times 10^{-7} \) nm/K\(^3\). We conclude that the electron-phonon coupling is the dominant contribution to the ZPL energy
shift.

We note, that the ZPL shifts to lower energy for decreasing temperature. This implies, that the phonon energies in the excited electronic state are larger than those in the ground electronic state. This is unusual because ground electronic wavefunction are usually more confined and thus lead to stiffer bonds and higher vibrational frequencies. We also note, that the error margin of the fit is in agreement with a dominant phonon coupling to the flexural mode polarization for temperatures below \( \approx 134 \text{ K} \) (see SI, section 2). Our model turns the overall PL ZPL broadening rate into an odd powered polynomial in temperature

\[
\Gamma_{ZPL} \approx d_{ZPL,1} T + d_{ZPL,3} T^3 + d_{ZPL,5} T^5 
\]

which is used to fit the experimental data. The linear term reflects the coupling to flexural modes, the cubic term is a product of couplings to flexural and shear/longitudinal modes, and the fifth powered term is due to shear/longitudinal modes. The fit parameters yield \( d_{ZPL,1} = 0.62 \text{ GHz/K} \), \( d_{ZPL,3} = 4.8 \times 10^{-5} \text{ GHz/K}^2 \) and \( d_{ZPL,5} = 7.5 \times 10^{-10} \text{ GHz/K}^3 \). Consistent with the ZPL shift, we conclude that the phonon coupling is dominated by the flexural mode polarization for temperatures below \( \approx 115 \text{ K} \) where the higher polynomial powers match the linear terms (see SI, section 2). The results are consistent with the much higher mode density of flexural modes at low frequency, which arises from their quadratic dispersion relationship.

We now turn our focus on the investigation of the optical transition under resonant excitation. Lifetime measurements show no temperature-dependence for different SPEs in hBN (see reference (15,24)). In order to investigate the temperature-dependence we first perform resonant excitation at 3 K (figure S4A-C). We tune the laser to the transition frequency of the emitter and record fluorescence as a function of time. We only collect phonon side band luminescence, using a long pass filter (see figure S1 for setup configurations). The resonant excitation signal shows an ongoing spectral diffusion (figure 3A, upper panel). For every dataset we evaluate a
signal threshold conditioned on a signal level being ten times above the noise level (see details in SI, section 3). We define the on and off states of the emitter with a threshold of around 1330 counts/s with a signal-to-noise separation of typically 6 standard deviations. Each jump in the fluorescence trace above this threshold corresponds to an emitter being on, meaning tuned on resonance with the excitation laser. We map the inhomogeneous linewidth arising from the spectral diffusion by determining the dependence of the excitation efficiency on the laser frequency detuning. The extracted inhomogeneous linewidth depends linearly on excitation power as depicted in figure 3 A (lower panel). By extrapolating to zero excitation power the inhomogeneous linewidth approaches the FT limit with the large error margin of 10 GHz.

The observation of slow blinking and diffusion that is linear in resonant laser power can be explained by two mechanisms. One, the direct excitation of the environment. For example, this could excite free carriers that are captured by the defect, sending it into a dark charge state (blinking), as well as other traps that change the local electric field of the defect (diffusion).

Two, non-radiative decay from the emitting state to a dark state. For example, this could be the tunneling of charge from the defect to a nearby trap, causing blinking. If the defect then captures a charge from a different trap, this will lead to a spectral shift.

We then repeat the experiment at 300 K as shown in Fig. 3B. The resonant excitation signal is again clearly visible. To confirm that the observed resonant excitation is not an artefact, we performed a control measurement. The excitation laser is detuned 2 nm to the the blue and the red spectral range, and under these conditions no excitation signal is observed (see fig. S4, S5).

We also note that these spectral jumps can not correspond to a different emitter at the same location, as the excitation power is not sufficient to excite emitters non-resonantly. Extrapolating the inhomogeneous linewidth at 300 K to zero excitation power yields the FT limit within an error margin of 50 GHz.

Finally, we explore the temperature-dependence of the homogeneous linewidth. We perform
Figure 3: Temperature-dependence in resonant photoluminescence excitation spectroscopy. A: Fluorescence timetrace under resonant excitation (upper panel) and power-dependency of the inhomogeneous linewidth (lower panel) at 3K. B: Fluorescence timetrace under resonant excitation (upper panel) and power-dependency of the inhomogeneous linewidth (lower panel) at 300K. A threshold (depicted in the fluorescence traces) is defined to distinguish between signal and noise and to estimate the amount of spectral diffusion that is the origin for inhomogeneous line broadening (details see SI section 3 and 4). The inhomogeneous linewidth shows a linear power dependency with a linewidth as broad as 773 GHz at 3K and 300 nW excitation power and 1.4 THz at 300 K. C: The homogeneous linewidth in PLE over temperature. The linewidth stays close to the FT limit of $60.1 \pm 3.4$ MHz in a temperature range from 3 K up to room temperature. The recorded PLE spectra with the Lorentzian fits are depicted for 3 K, 100 K, 200 K and 300 K.
resonant PLE measurements for a temperature range between 3 K and 300 K as shown in Figure 3C. A Lorentzian fit to the data is shown for 3K, 100K, 200K and 300K. In each case the linewidth is approaching within the FT limit range (within the error margins of the experiments). Remarkably, as the temperature increases, the linewidth remains below 100 MHz. Note that each of the dot points corresponds to the system being on resonance, and the evidence of lorentzian fit exemplifies the true linewidth, rather than a random spectral jump that would not have had a symmetrical profile. A detailed analysis of the linewidth-dependence on the scan speed and on the blinking timescale (see (25)) is given in the SI, section 5.

The lack of temperature dependent broadening of the PLE ZPL implies that there is no coupling to low frequency acoustic phonons or any other dephasing under resonant excitation on the timescale of the scans of 0.03 s. In the absence of piezoelectricity, this indicates that the defect is mechanically isolated in the ground and emitting excited states. This is, to our knowledge, the only solid-state based SPE without any sign of dephasing or electron-phonon interaction in the excitation process at room temperature. The absence of coupling to acoustic phonons is consistent with the coupling to high frequency optical phonons that yields the PSB feature that is used for PLE detection. The optical phonons will not yield a temperature dependence until very high temperatures, owing to their high frequencies. The optical phonons can couple to the defect at a distance due to the electric fields generated by their dynamic polarization. Thus, they do not require mechanical contact.

The interpretation of the stark difference between line broadening under resonant excitation (PLE) and off-resonant excitation (PL) is non trivial. We propose two possible explanations: (1) activation of electron-phonon interactions via far off-resonance excitation of another electronic state. As demonstrated above, explanation (1) is consistent with the line broadening and line shift observed in PL. It is also consistent with the triangular lineshape of the PL PSB (26-28). The high frequency components of the PL PSB can be explained by similar coupling to optical
phonons as under resonant excitation. However, the precise mechanism of the third electronic state ‘activating’ the electron-phonon interactions is not obvious and is unusual. Explanation (2) doesn’t involve electron-phonon interactions. Rather, it claims that the ZPL and low-frequency sideband in PL is actually the distribution of spectral diffusion. The off-resonant excitation could enhance spectral diffusion that leads to faster cycling of the photoblinking/diffusion mechanism as well as greater diversity of spectral shifts. The sideband near the ZPL would then represent the spectral diffusion distribution, rather than the spectral density of acoustic electron-phonon interactions. This enhanced cycling and range of spectral shifts could be enabled by the additional electronic state and may be temperature dependent. From our work, it is not possible to distinguish between the two explanations: (1) is supported by the agreement of our electron-phonon model with the PL ZPL shift and broadening with temperature, and (2) is extrapolated from the spectral diffusion behaviour we observed in PLE. To resolve this unusual problem, future experimental work should seek to better understand the off-resonance excitation mechanism, confirm the existence of a third electronic state, and further theoretical work should develop possible models for the activation of electron-phonon interactions and temperature dependent spectral diffusion that are consistent with our observations.

In the presented work we demonstrate FT limited lines in the excitation process of SPEs in hBN at room temperature. Our findings open new prospects for room temperature quantum optics experiments in the fields of quantum information processing and precision sensing. In the context of novel quantum materials our platform enables to combine the attractive mechanical, electrical, thermal and chemical (23) properties of two-dimensional materials with the atom-like optical properties of a quantum emitter at room temperature. hBN is a key component in many van der Waals heterostructures, and can now be combined with ideal SPEs, e.g. for photon-mediated interactions. The list of novel room temperature applications include quantum photonics interfacing hBN membranes with classical photonics as well as large variety of
hybrid quantum systems based on quantum emitters in hBN owing to the large spread of emission frequencies and high integrateability. Ongoing spectral diffusion leads to a low excitation efficiency at room temperature. It can be solved by surface termination or by embedding the two-dimensional material into a protecting host matrix.

References


Acknowledgments

AK acknowledges the generous support of the DFG, the Carl-Zeiss Foundation, IQST, the Wissenschaftler-Rückkehrprogramm GSO/GZS and the EFRE-Programm Baden-Württemberg. I.A. acknowledges the generous support of the Alexander van Humboldt foundation, and the Asian Office of Aerospace Research & Development (grant # FA2386-17-1-4064), the Office of Naval Research Global (grant # N62909-18-1-2025) and the Australian Research Council (DP180100077). M.W.D. acknowledges support from the Australian Research Council (DE170100169). We thank Fedor Jelezko, Stefan Häuler and Michael Höse for fruitful discussion and experimental support.

Supplementary materials

Materials and Methods
Supplementary Text
Figs. S1 to S11